

Product Summary

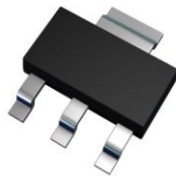
BV_{DSS}	$R_{DS(ON)}$ max	I_D $T_A = +25^\circ C$
-100V	350m Ω @ $V_{GS} = -10V$	-2.4A
	450m Ω @ $V_{GS} = -6V$	-2.1A

Description and Applications

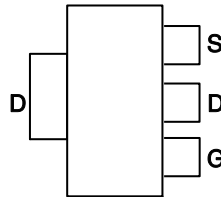
This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor Control
- DC-DC Converters
- Power Management Functions
- Relay and Solenoid Driving

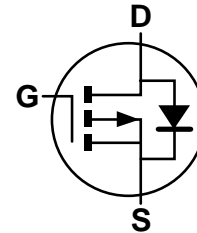
SOT223



Top View



Pin Out - Top View



Equivalent Circuit

Features and Benefits

- Fast Switching Speed
- Low Input Capacitance
- Low Gate Drive
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

Mechanical Data

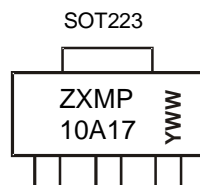
- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.112 grams (Approximate)

Ordering Information (Note 5)

Part Number	Case	Packaging
ZXMP10A17GQTA	SOT223	1,000/Tape & Reel
ZXMP10A17GQTC	SOT223	4,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
 5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



ZXMP10A17 = Product Type Marking Code
 YWW = Date Code Marking
 Y = Year (ex: 7 = 2017)
 WW = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-100	V
Gate-Source Voltage			V _{GS}	±20	V
Continuous Drain Current	V _{GS} = -10V	(Note 7)	I _D	-2.4	A
		T _A = +70°C (Note 7)		-1.9	
		(Note 6)		-1.7	
Pulsed Drain Current	V _{GS} = -10V	(Note 8)	I _{DM}	-9.4	A
Continuous Source Current (Body Diode)			I _S	-4.5	A
Pulsed Source Current (Body Diode)			I _{SM}	-9.4	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

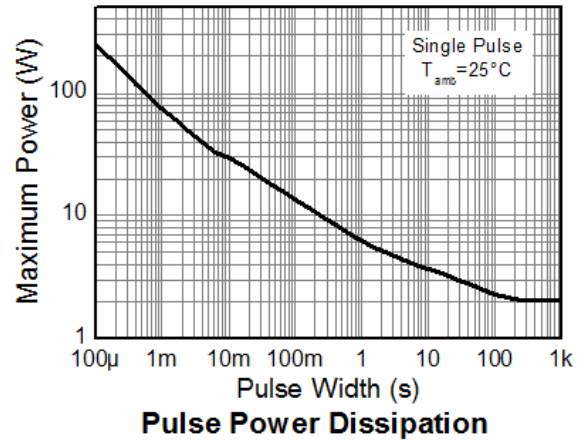
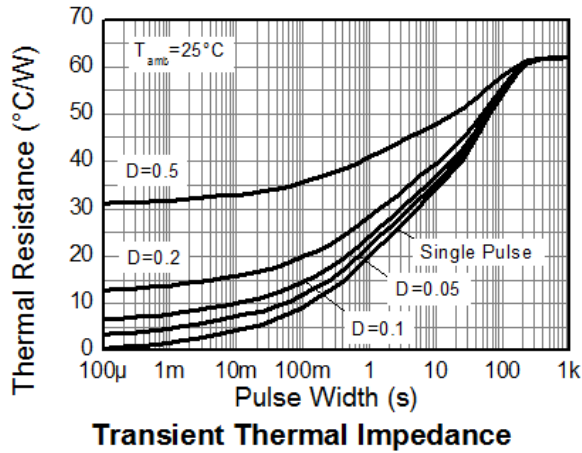
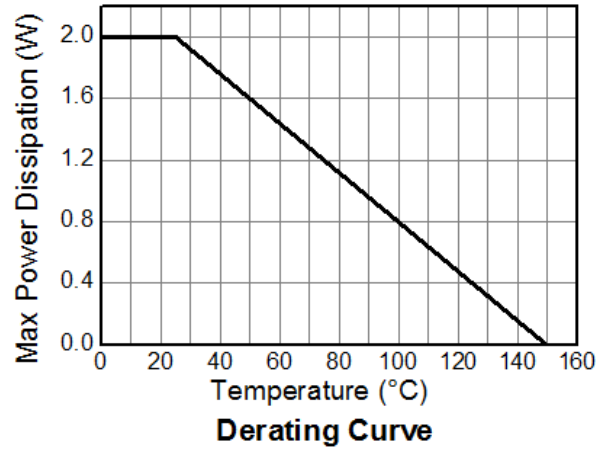
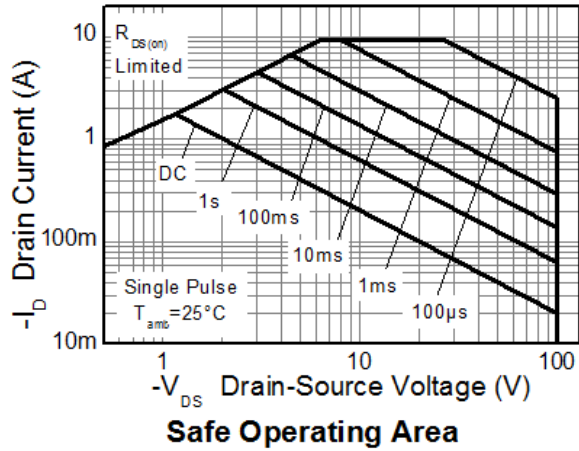
Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 6)	P _D	2.0	W
	Linear Derating Factor		16	
	(Note 7)		3.9	
			31	
Thermal Resistance, Junction to Ambient	(Note 6)	R _{θJA}	62.5	°C/W
	(Note 7)		32.0	
Thermal Resistance, Junction to Case	(Note 6)	R _{θJC}	7.7	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

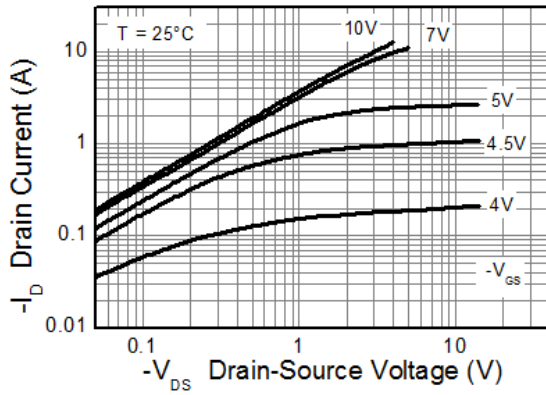
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	-100	—	—	V	I _D = -250μA, V _{GS} = 0V
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-0.5	μA	V _{DS} = -100V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	-2.0	—	-4.0	V	I _D = -250μA, V _{DS} = V _{GS}
Static Drain-Source On-Resistance (Note 9)	R _{DS(ON)}	—	—	0.350	Ω	V _{GS} = -10V, I _D = -1.4A
				0.450		V _{GS} = -6V, I _D = -1.2A
Forward Transconductance (Notes 9 & 10)	g _{fs}	—	2.8	—	S	V _{DS} = -15V, I _D = -1.4A
Diode Forward Voltage (Note 9)	V _{SD}	—	-0.85	-0.95	V	I _S = -1.7A, V _{GS} = 0V
Reverse Recovery Time (Note 10)	t _{RR}	—	33	—	ns	I _F = -1.5A, di/dt = 100A/μs
Reverse Recovery Charge (Note 10)	Q _{RR}	—	48	—	nC	
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	—	424	—	pF	V _{DS} = -50V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{oss}	—	36.6	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	29.8	—	pF	
Total Gate Charge (Note 11)	Q _g	—	7.1	—	nC	V _{GS} = -6.0V
Total Gate Charge (Note 11)	Q _g	—	10.7	—	nC	V _{GS} = -10V V _{DS} = -50V I _D = -1.4A
Gate-Source Charge (Note 11)	Q _{gs}	—	1.7	—	nC	
Gate-Drain Charge (Note 11)	Q _{gd}	—	3.8	—	nC	
Turn-On Delay Time (Note 11)	t _{D(ON)}	—	3.0	—	ns	V _{DD} = -15V, V _{GS} = -10V I _D = -1A, R _G ≅ 6.0Ω
Turn-On Rise Time (Note 11)	t _R	—	3.5	—	ns	
Turn-Off Delay Time (Note 11)	t _{D(OFF)}	—	13.4	—	ns	
Turn-Off Fall Time (Note 11)	t _F	—	7.2	—	ns	

- Notes:
6. For a device surface mounted on 25mm x 25mm x 1.6mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 7. Same as Note 6, except the device is measured at t ≤ 10 seconds.
 8. Same as Note 6, except the device is pulsed with D = 0.02 and pulse width 300μs. The pulse current is limited by the maximum junction temperature.
 9. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%.
 10. For design aid only, not subject to production testing.
 11. Switching characteristics are independent of operating junction temperatures.

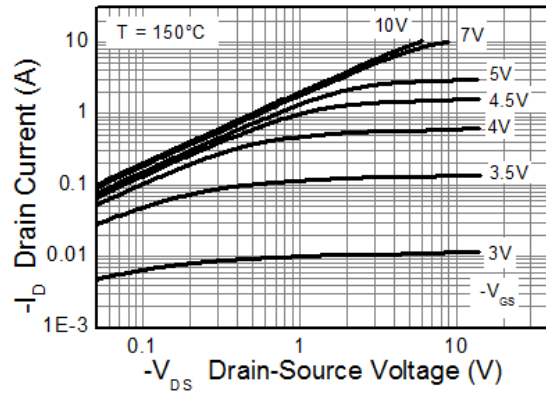
Thermal Characteristics



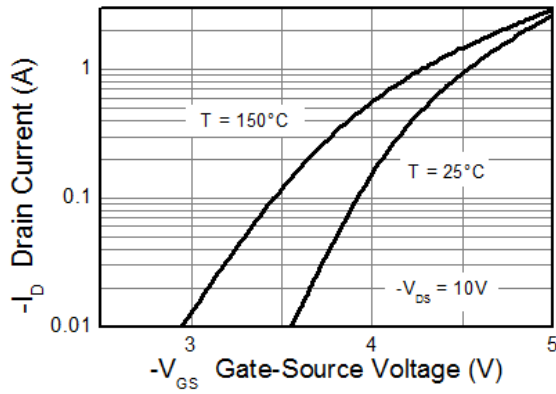
Typical Characteristics (Cont.)



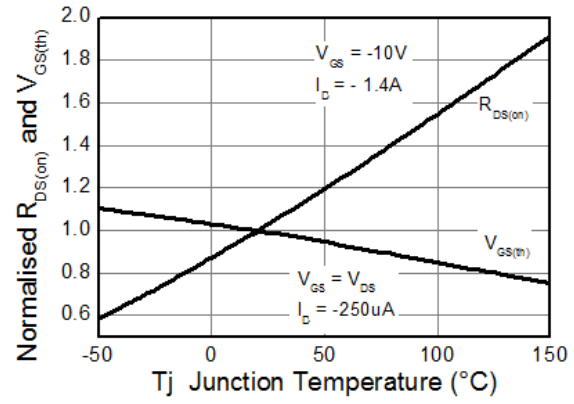
Output Characteristics



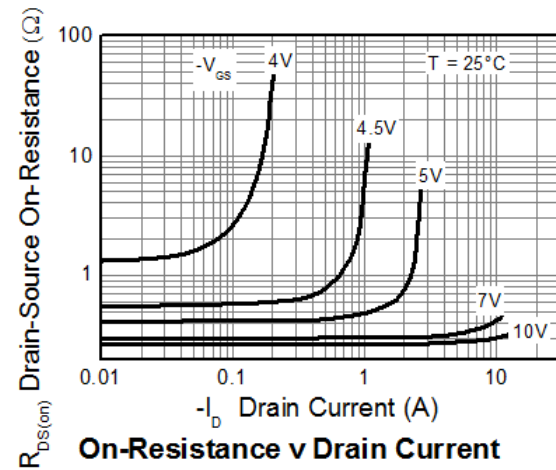
Output Characteristics



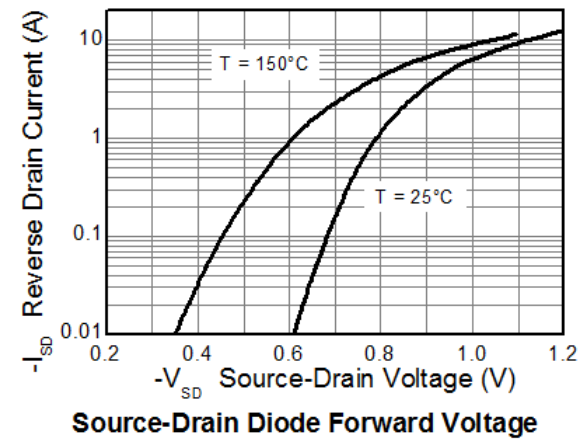
Typical Transfer Characteristics



Normalised Curves v Temperature



On-Resistance v Drain Current

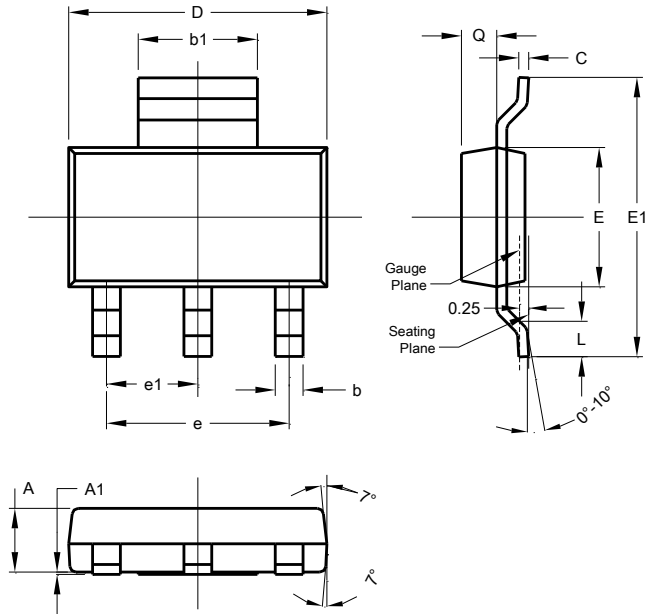


Source-Drain Diode Forward Voltage

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT223

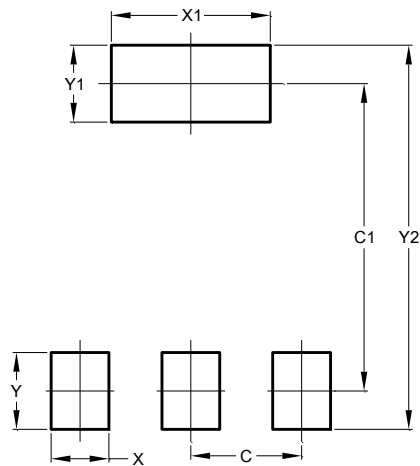


SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT223



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

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